IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~strikethrough~~.

Please REPLACE paragraph [0014] with the following paragraph:

Furthermore, it is disclosed in U.S. Patent No. ~~6,177,391~~6,177,301 that the barrier effect of crystal grain boundaries for the direction of an electric charge carrier is minimized (FIG. 3A), and TFT characteristics being second to single crystalline silicon is obtained accordingly in the case where the direction of active channels is parallel to the direction of crystal grains grown by the SLS crystallization method when fabricating a TFT for an LCD comprising driver and pixel arrays by forming large silicon grains using SLS crystallization technology while a lot of crystal grain boundaries in which the TFT characteristics acts as a trap for the electric charge carriers exist, and the TFT characteristics is greatly deteriorated in the case where the active channel direction is perpendicular to the crystal grain growing direction (FIG. 3B).